

ORGANO-ELECTRONIC DEVICE AND ITS FABRICATING METHOD

Patent number: JP2003258164

Publication date: 2003-09-12

Inventor: HORIUCHI KAZUNAGA; SHIMIZU MASAAKI; OCHIAI YUICHI; AOKI NOBUYUKI

Applicant: FUJI XEROX CO LTD

Classification:

- **international:** H01L23/29; H01L21/316; H01L23/31; H01L29/06; H01L29/786; H01L51/00

- **european:**

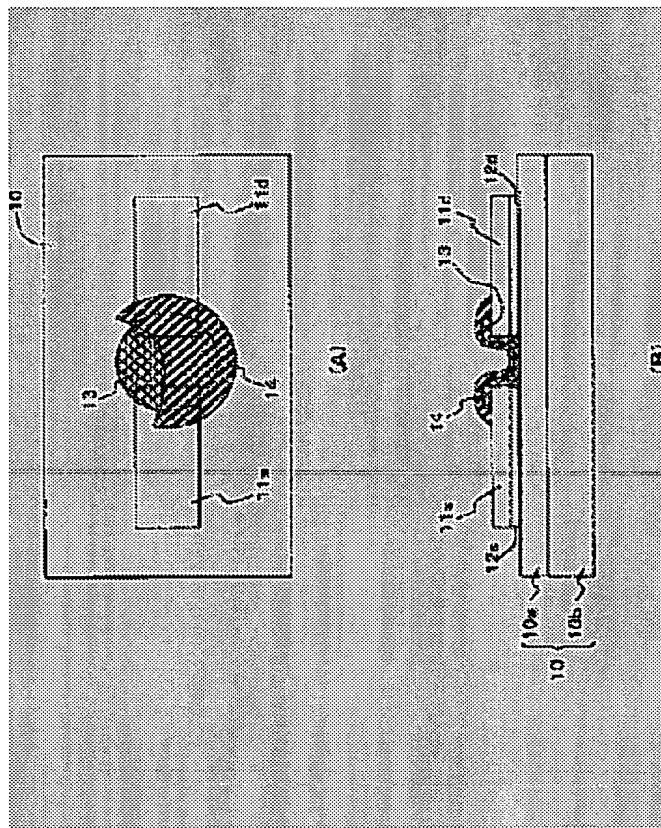
Application number: JP20020055299 20020301

Priority number(s): JP20020055299 20020301

[Report a data error here](#)

Abstract of JP2003258164

<P>**PROBLEM TO BE SOLVED:** To provide an organo-electronic device in which variation or deterioration of characteristics due to atmosphere is improved, and a method for fabricating an organo-electronic device conveniently at a low cost. <P>**SOLUTION:** The organo-electronic device has an organo-electronic material layer 13 where at least a part of the organo-electronic material layer 13 is sealed with an alumina sealing film 14. In the method for fabricating an organo-electronic device, the sealing film 14 is formed by depositing an alumina film at a part being sealed with the sealing film 14 using an RF sputtering system. <P>**COPYRIGHT:** (C) 2003,JPO



Data supplied from the esp@cenet database - Worldwide